

# RBN25H125S1FPQ-A0

1250V - 25A - IGBT  
Power Switching

R07DS1378EJ0132  
Rev.1.32  
Jun 19, 2019

## Features

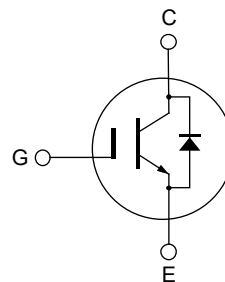
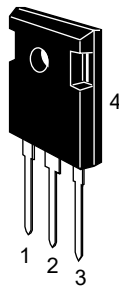
- Trench gate and thin wafer technology (G8H series)
- Built in fast recovery diode in one package
- Low collector to emitter saturation voltage  
 $V_{CE(sat)} = 1.8 \text{ V typ. (at } I_C = 25 \text{ A, } V_{GE} = 15 \text{ V, } T_a = 25^\circ\text{C)}$
- Quality grade: Standard
- High speed switching
- Short circuit withstands time (10  $\mu\text{s min.}$ )
- Applications: UPS, Welding, photovoltaic inverters, Power converter system

## Key Performance

Type	V <sub>CE</sub> S	I <sub>C</sub>	V <sub>CE(sat)</sub> , T <sub>C</sub> =25°C	I <sub>F</sub>	t <sub>sc</sub>	T <sub>j</sub>
RBN25H125S1FPQ-A0	1250 V	25 A	1.8 V	15 A	10 $\mu\text{s}$	175 °C

## Outline

RENESAS Package code: PRSS0003ZH-A  
(Package name: TO-247A)



1. Gate
2. Collector
3. Emitter
4. Collector

**Absolute Maximum Ratings**(T<sub>c</sub> = 25 °C)

Item	Symbol	Ratings	Unit
Collector to emitter voltage	V <sub>CES</sub>	1250	V
Gate to emitter voltage	V <sub>GES</sub>	±30	V
Collector current	T <sub>c</sub> = 25 °C	I <sub>C</sub>	50
	T <sub>c</sub> = 100 °C	I <sub>C</sub>	25
Collector peak current	I <sub>C(peak)</sub> <sup>Note1</sup>	100	A
Diode forward current	T <sub>c</sub> = 25 °C	I <sub>F</sub>	30
	T <sub>c</sub> = 100 °C	I <sub>F</sub>	15
Diode forward peak current	I <sub>F(peak)</sub> <sup>Note1</sup>	100	A
Collector power dissipation	P <sub>C</sub> <sup>Note 2</sup>	223	W
Junction temperature	T <sub>J</sub> <sup>Note2</sup>	175	°C
Storage temperature	T <sub>stg</sub>	-55 to +150	°C

Note: Continuous heavy condition (e.g. high temperature/voltage/current or high variation of temperature) may affect a reliability even if it are within the absolute maximum ratings. Please consider derating condition for appropriate reliability in reference Renesas Semiconductor Reliability Handbook (Recommendation for Handling and Usage of Semiconductor Devices) and individual reliability data.

Notes: 1. PW ≤ 10 μs, duty cycle ≤ 1 %

2. Please use this device in the thermal conditions which the junction temperature does not exceed 175 °C. Renesas IGBT Application Note is disclosed about reliability test and application condition up to 175 °C.

**Thermal Resistance Characteristics**

Item	Symbol	Max. Value <sup>Note3</sup>	Unit
Junction to case thermal resistance (IGBT)	R <sub>th(j-c)</sub>	0.67	°C/W
Junction to case thermal resistance (Diode)	R <sub>th(j-c)</sub>	2.10	°C/W

Notes: 3. This data is the designed target maximum value on Renesas's measurement condition.

## Electrical Characteristics

(T<sub>c</sub> = 25 °C)

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Collector to emitter leakage current	I <sub>CEs</sub>	—	—	200	μA	V <sub>CE</sub> = 1250 V, V <sub>GE</sub> = 0 V
Gate to emitter leakage current	I <sub>GES</sub>	—	—	±1	μA	V <sub>GE</sub> = ±30 V, V <sub>CE</sub> = 0 V
Gate to emitter threshold voltage	V <sub>GE(th)</sub>	5.3	—	7.1	V	V <sub>CE</sub> = 10 V, I <sub>c</sub> = 0.83 mA
Collector to emitter saturation voltage	V <sub>CE(sat)</sub>	—	1.8	2.34	V	I <sub>c</sub> = 25 A, V <sub>GE</sub> = 15 V <sup>Note4</sup>
Input capacitance	C <sub>ies</sub>	—	1540	—	pF	V <sub>CE</sub> = 25 V
Output capacitance	C <sub>oes</sub>	—	78	—	pF	V <sub>GE</sub> = 0 V
Reverse transfer capacitance	C <sub>res</sub>	—	12	—	pF	f = 1 MHz
Total gate charge	Q <sub>g</sub>	—	56	—	nC	V <sub>GE</sub> = 15 V
Gate to emitter charge	Q <sub>ge</sub>	—	16	—	nC	V <sub>CE</sub> = 600 V
Gate to collector charge	Q <sub>gc</sub>	—	29	—	nC	I <sub>c</sub> = 25 A
Turn-on delay time	t <sub>d(on)</sub>	—	19	—	ns	V <sub>CC</sub> = 600 V
Rise time	t <sub>r</sub>	—	8	—	ns	V <sub>GE</sub> = 15 V/-15 V
Turn-off delay time	t <sub>d(off)</sub>	—	109	—	ns	I <sub>c</sub> = 25 A
Fall time	t <sub>f</sub>	—	58	—	ns	R <sub>g</sub> = 10 Ω
Turn-on loss energy	E <sub>on</sub>	—	1.1	—	mJ	T <sub>c</sub> = 25 °C
Turn-off loss energy	E <sub>off</sub>	—	0.8	—	mJ	Inductive load <sup>Note5</sup>
Total switching energy	E <sub>total</sub>	—	1.9	—	mJ	
Turn-on delay time	t <sub>d(on)</sub>	—	20	—	ns	V <sub>CC</sub> = 600 V
Rise time	t <sub>r</sub>	—	9	—	ns	V <sub>GE</sub> = 15 V/-15 V
Turn-off delay time	t <sub>d(off)</sub>	—	132	—	ns	I <sub>c</sub> = 25 A
Fall time	t <sub>f</sub>	—	70	—	ns	R <sub>g</sub> = 10 Ω
Turn-on loss energy	E <sub>on</sub>	—	1.8	—	mJ	T <sub>c</sub> = 150 °C
Turn-off loss energy	E <sub>off</sub>	—	1.4	—	mJ	Inductive load <sup>Note5</sup>
Total switching energy	E <sub>total</sub>	—	3.2	—	mJ	
Short circuit withstand time <sup>Note6</sup>	T <sub>sc</sub>	10	—	—	μs	V <sub>CC</sub> ≤ 720 V, V <sub>GE</sub> = 15 V T <sub>c</sub> ≤ 150 °C

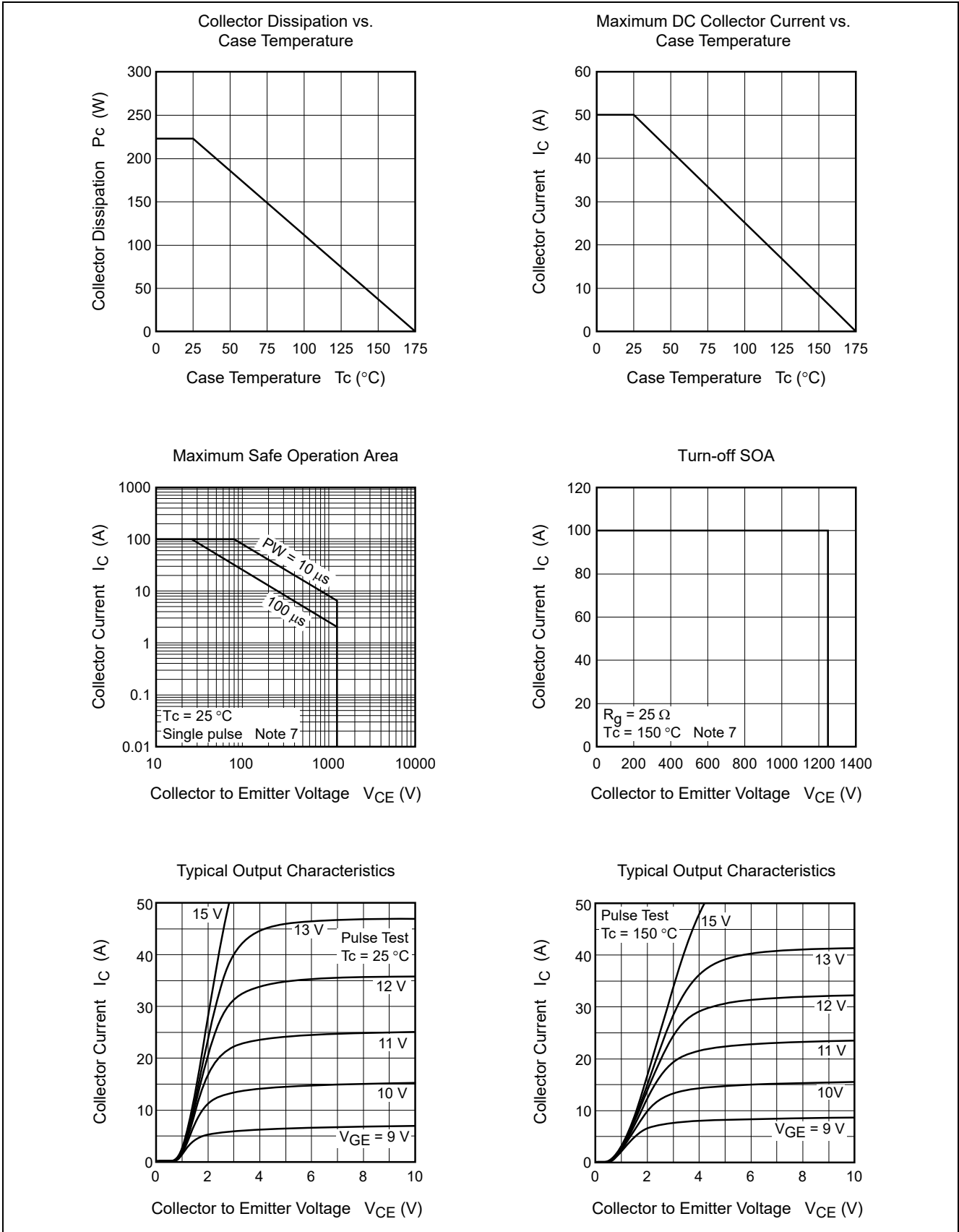
Diode forward voltage	V <sub>F</sub>	—	2.9	3.77	V	I <sub>F</sub> = 15 A <sup>Note4</sup>
Diode reverse recovery time	t <sub>rr</sub>	—	102	—	ns	I <sub>F</sub> = 15 A, di <sub>F</sub> /dt = 300 A/μs
Diode reverse recovery charge	Q <sub>rr</sub>	—	0.53	—	μC	
Diode peak reverse recovery current	I <sub>rr</sub>	—	9	—	A	

Notes: 4. Pulse test

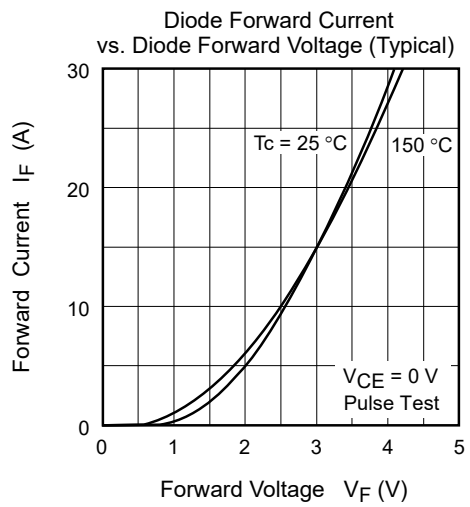
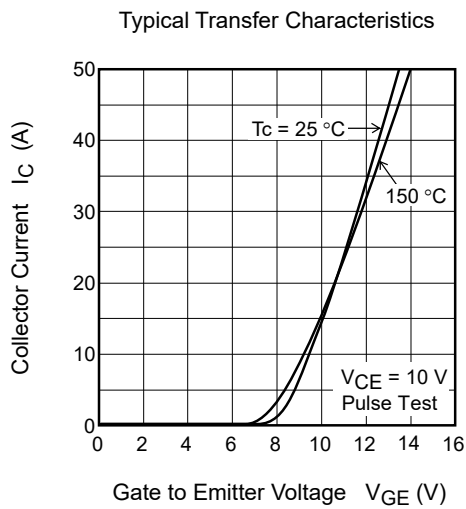
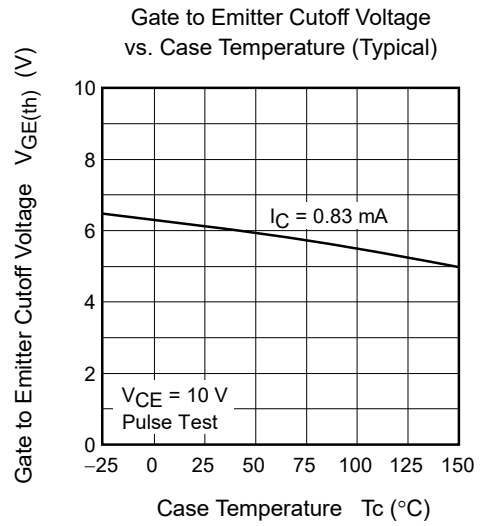
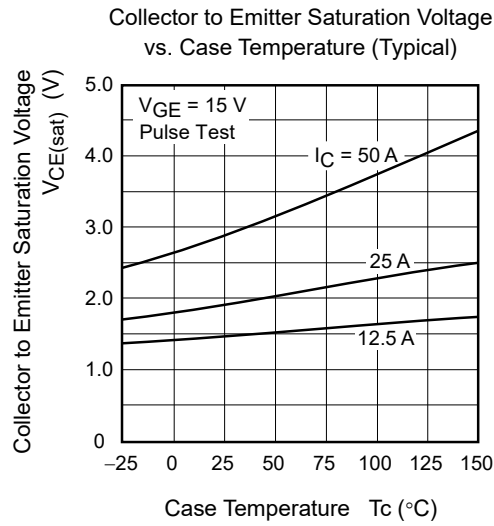
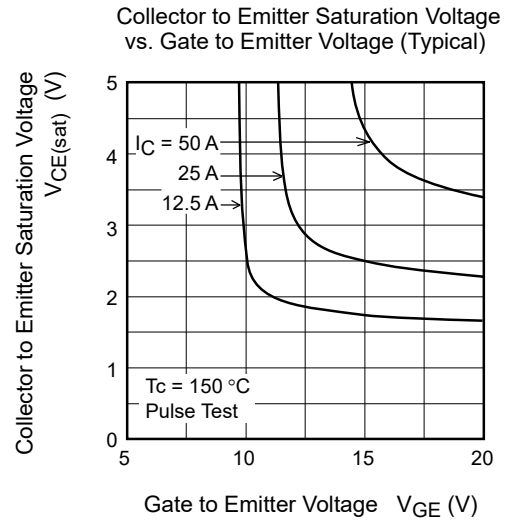
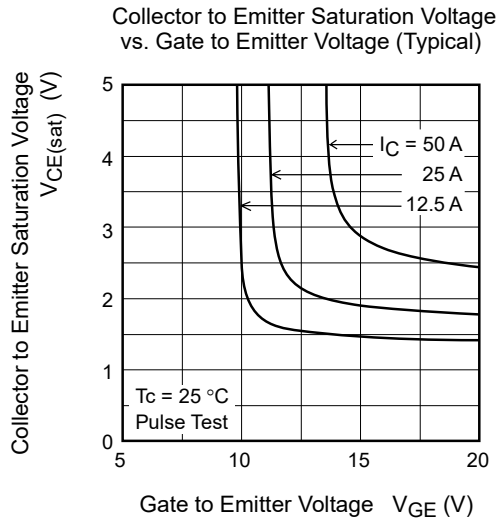
5. Switching time test circuit and waveform are shown below.

6. Verified by design.

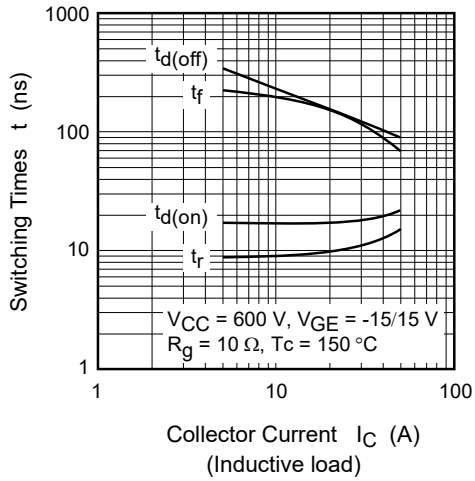
### Main Characteristics



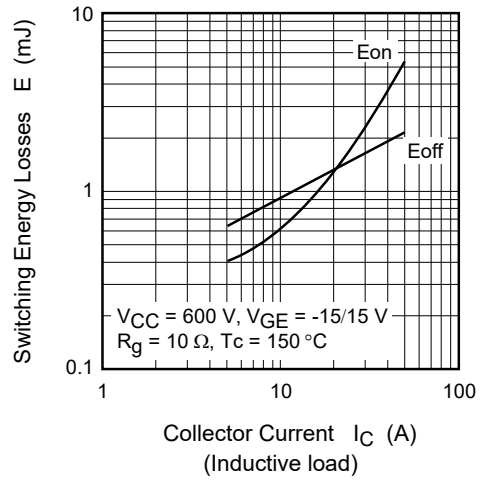
Notes: 7. This data is the designed value on Renesas's measurement condition, Renesas recommends that operating conditions are designed according to a document "Power MOS FET · IGBT Attention of Handling Semiconductor Devices".



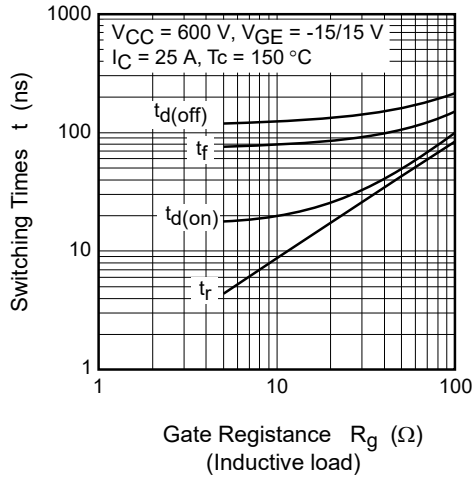
Switching Characteristics (Typical) (1)



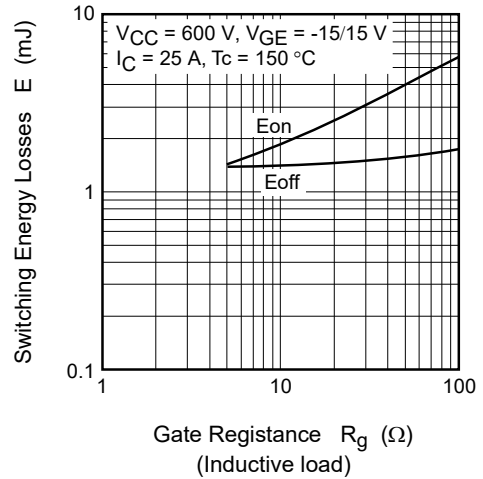
Switching Characteristics (Typical) (2)



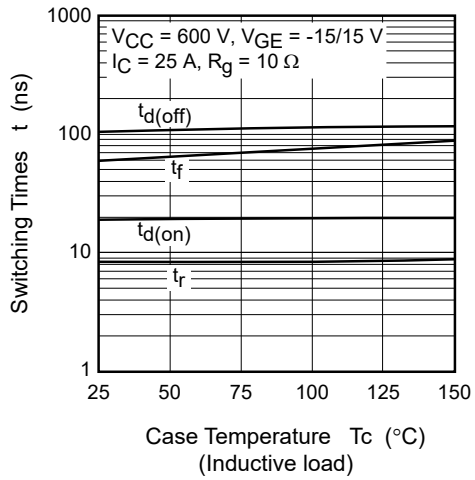
Switching Characteristics (Typical) (3)



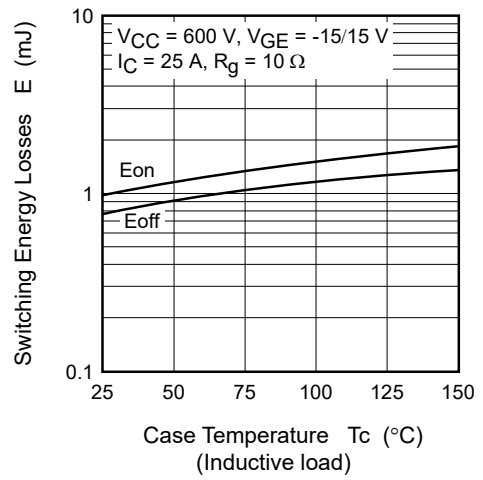
Switching Characteristics (Typical) (4)

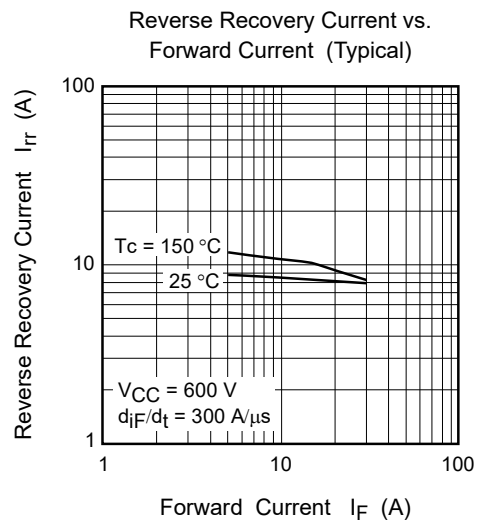
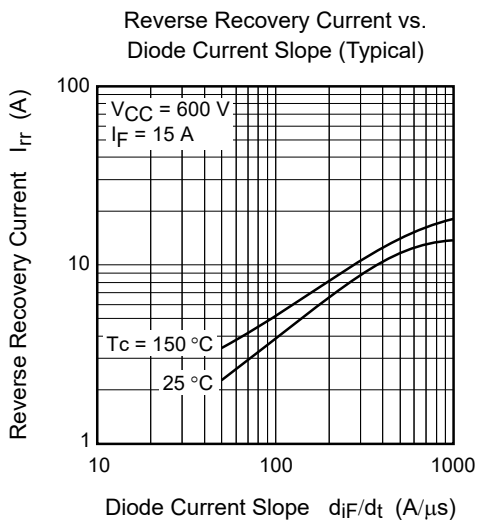
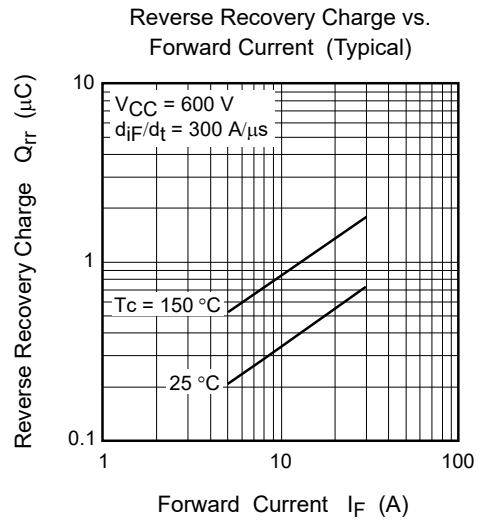
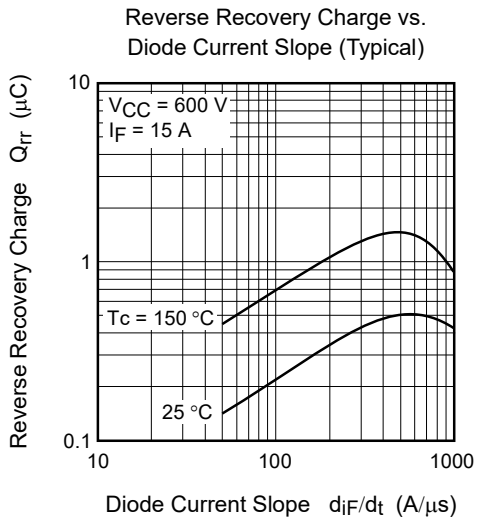
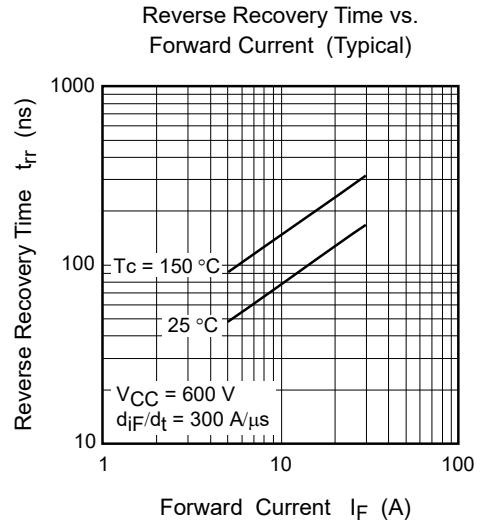
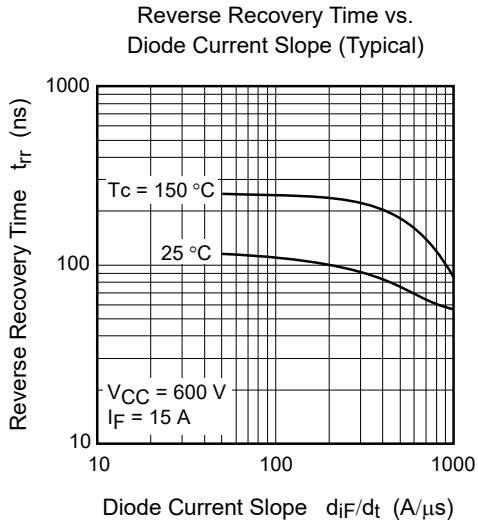


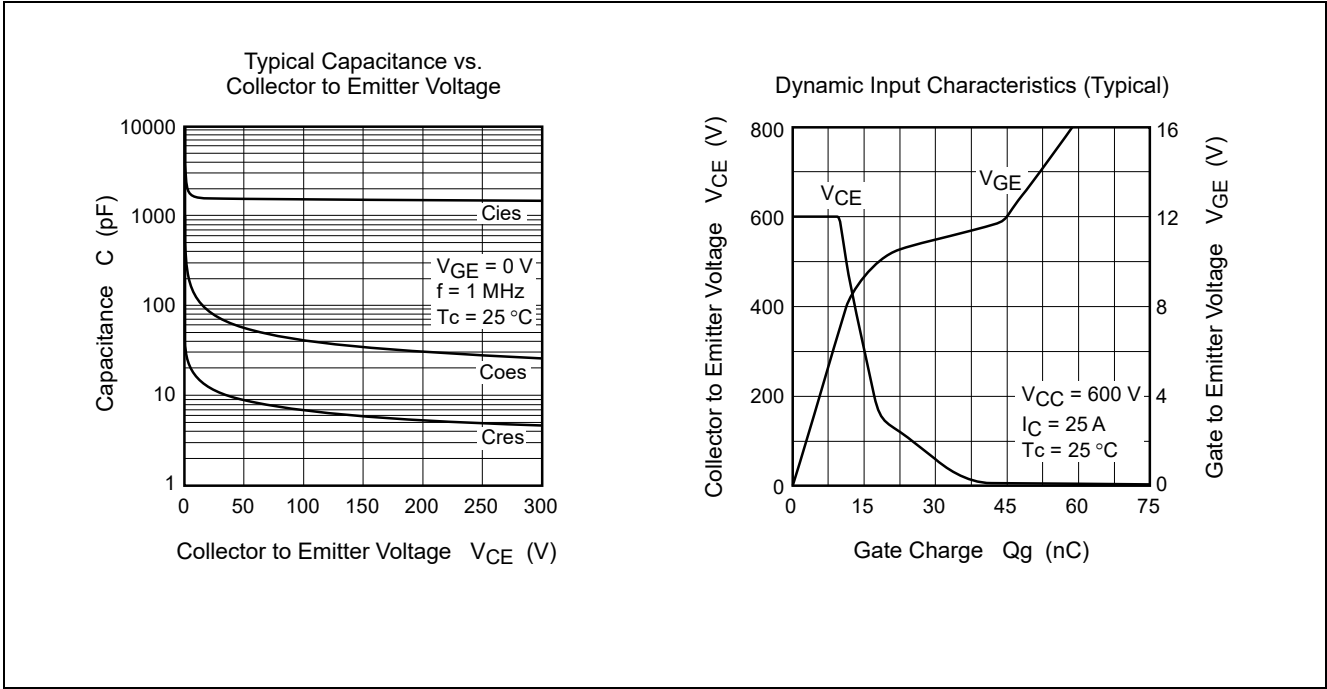
Switching Characteristics (Typical) (5)



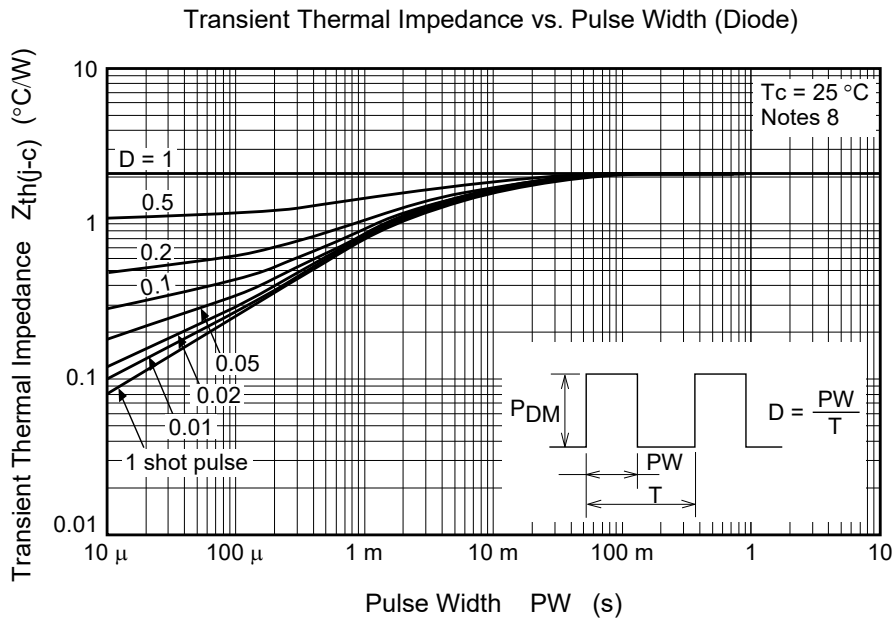
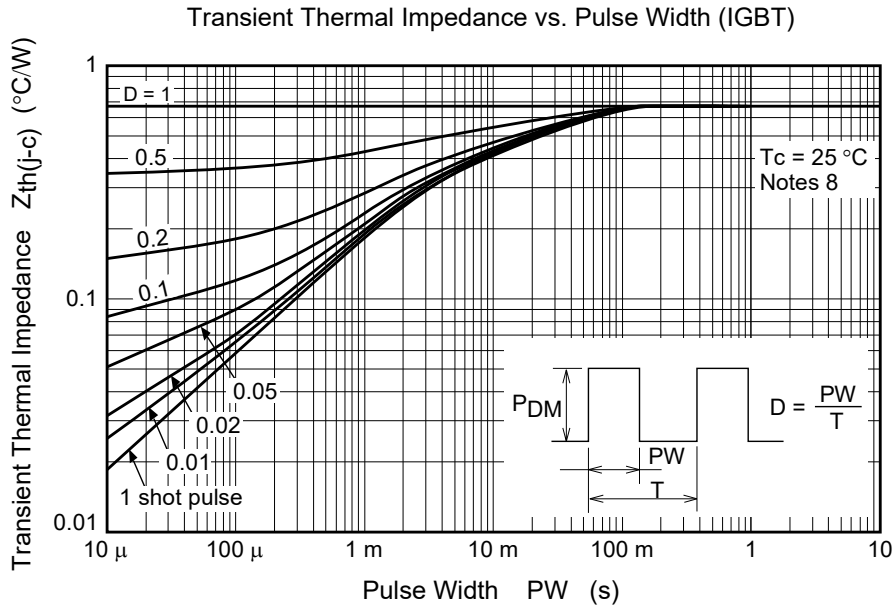
Switching Characteristics (Typical) (6)





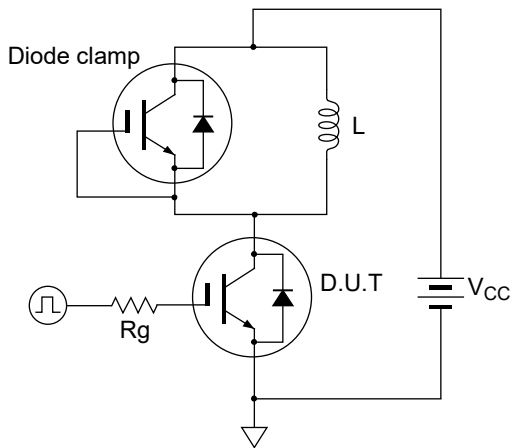




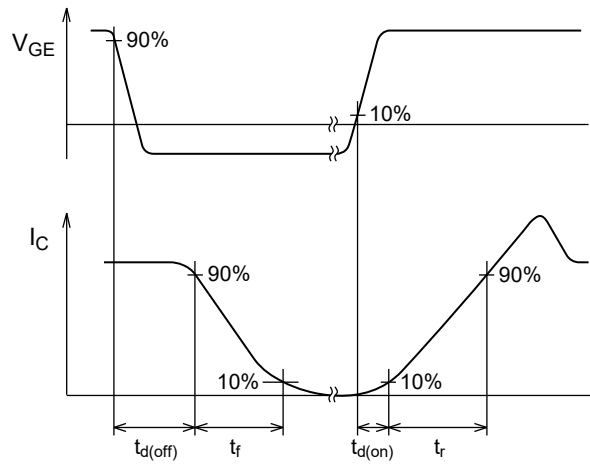


Notes: 8. This data is the designed target maximum value on Renesas's measurement condition.

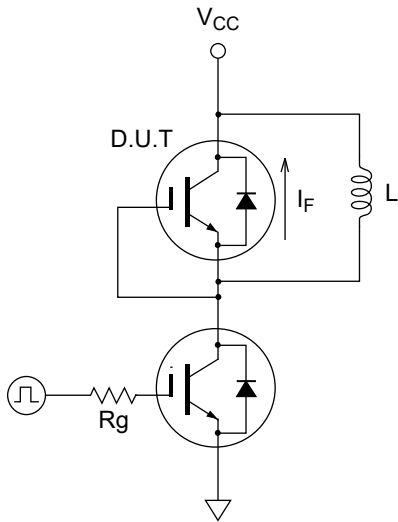
Switching Time Test Circuit



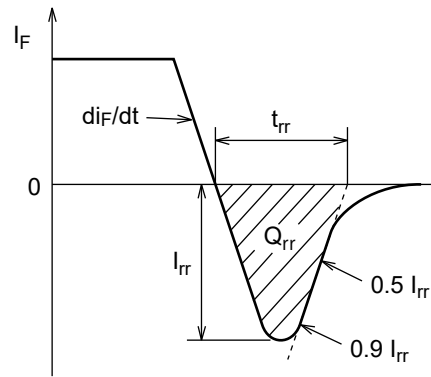
Waveform



Diode Reverse Recovery Time Test Circuit



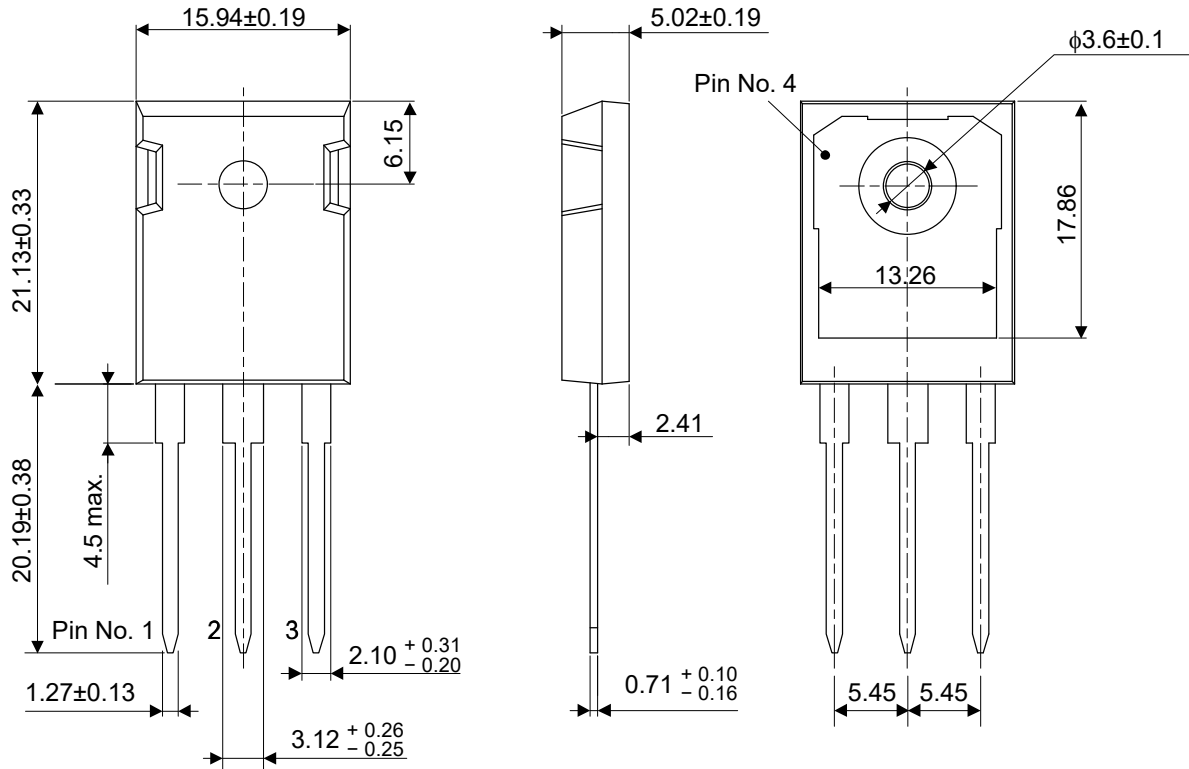
Waveform



### Package Dimensions

JEDEC Package Code	RENESAS Code	Previous Code	MASS (Typ) [g]
TO-247AD	PRSS0003ZH-A	—	6.14

Unit: mm



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### Ordering Information

Orderable Part Number	Quantity	Shipping Container
RBN25H125S1FPQ-A0#CB0	240 pcs	Box (Tube)

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TOYOSU FORESIA, 3-2-24 Toyosu, Koto-ku, Tokyo 135-0061, Japan

#### Renesas Electronics America Inc.

1001 Murphy Ranch Road, Milpitas, CA 95035, U.S.A.  
Tel: +1-408-432-8888, Fax: +1-408-434-5351

#### Renesas Electronics Canada Limited

9251 Yonge Street, Suite 8309 Richmond Hill, Ontario Canada L4C 9T3  
Tel: +1-905-237-2004

#### Renesas Electronics Europe Limited

Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K  
Tel: +44-1628-651-700

#### Renesas Electronics Europe GmbH

Arcadiastrasse 10, 40472 Düsseldorf, Germany  
Tel: +49-211-6503-0, Fax: +49-211-6503-1327

#### Renesas Electronics (China) Co., Ltd.

Room 1709 Quantum Plaza, No.27 ZhichunLu, Haidian District, Beijing, 100191 P. R. China  
Tel: +86-10-8235-1155, Fax: +86-10-8235-7679

#### Renesas Electronics (Shanghai) Co., Ltd.

Unit 301, Tower A, Central Towers, 555 Langao Road, Putuo District, Shanghai, 200333 P. R. China  
Tel: +86-21-2226-0888, Fax: +86-21-2226-0999

#### Renesas Electronics Hong Kong Limited

Unit 1601-1611, 16/F., Tower 2, Grand Century Place, 193 Prince Edward Road West, Mongkok, Kowloon, Hong Kong  
Tel: +852-2265-6688, Fax: +852 2886-9022

#### Renesas Electronics Taiwan Co., Ltd.

13F, No. 363, Fu Shing North Road, Taipei 10543, Taiwan  
Tel: +886-2-8175-9600, Fax: +886 2-8175-9670

#### Renesas Electronics Singapore Pte. Ltd.

80 Bendemeer Road, Unit #06-02 Hyflux Innovation Centre, Singapore 339949  
Tel: +65-6213-0200, Fax: +65-6213-0300

#### Renesas Electronics Malaysia Sdn.Bhd.

Unit 1207, Block B, Menara Amcorp, Amcorp Trade Centre, No. 18, Jln Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia  
Tel: +60-3-7955-9390, Fax: +60-3-7955-9510

#### Renesas Electronics India Pvt. Ltd.

No.777C, 100 Feet Road, HAL 2nd Stage, Indiranagar, Bangalore 560 038, India  
Tel: +91-80-67208700, Fax: +91-80-67208777

#### Renesas Electronics Korea Co., Ltd.

17F, KAMCO Yangjae Tower, 262, Gangnam-daero, Gangnam-gu, Seoul, 06265 Korea  
Tel: +82-2-558-3737, Fax: +82-2-558-5338